ABSTRACT OF THE DISCLOSURE

In the fabricating of a light emitting device, a light emitting layer portion 24 and a current spreading layer 7, respectively composed of a Group III-V compound semiconductor, are stacked on a single crystal substrate. The light emitting layer portion 24 is formed by a metal organic vapor-phase epitaxy process, and the current spreading layer 7, on such light emitting layer portion 24, is formed to have conductivity type of n-type by a hydride vapor-phase epitaxy process.